



NCE N-Channel Enhancement Mode Power MOSFET

Description

The NCE0224A uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

- $V_{DS} = 200V, I_D = 24A$ $R_{DS(ON)} < 80m\Omega @ V_{GS} = 10V$ (Typ:62m Ω)
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% ΔVds TESTED!



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Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE0224A	NCE0224A	TO-220-3L	-	-	-

Absolute Maximum Ratings (T_c=25℃ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	Vds	200	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	Ι _D	24	A
Drain Current-Continuous(Tc=100℃)	I _D (100℃)	17	A
Pulsed Drain Current	I _{DM}	100	A
Maximum Power Dissipation	P _D	150	W
Single pulse avalanche energy (Note 5)	E _{AS}	250	mJ
Operating Junction and Storage Temperature Range	T _J ,T _{STG}	-55 To 175	°C





Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note 2) RI°C/W

Electrical Characteristics (T_c=25[°]C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics	· ·					
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	200	220	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =200V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20V, V_{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)	· ·					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS}$, $I_{D}=250\mu A$	1.0	1.5	2.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =15A	-	62	80	mΩ
Forward Transconductance	g fs	V _{DS} =10V,I _D =15A	30	-	-	S
Dynamic Characteristics (Note4)	L		-			•
Input Capacitance	C _{lss})/ _25)/)/ _0)/		4200		PF
Output Capacitance	Coss	V _{DS} =25V,V _{GS} =0V, F=1.0MHz		163		PF
Reverse Transfer Capacitance	Crss			75		PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	10	-	nS
Turn-on Rise Time	tr	V_{DD} =100V, I_{D} =15A	-	18	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10V, R_{GEN} =2.5 Ω	-	22	-	nS
Turn-Off Fall Time	t _f		-	5	-	nS
Total Gate Charge	Qg)/ _100)/ _15A		60		nC
Gate-Source Charge	Q _{gs}	V _{DS} =100V,I _D =15A, V _{GS} =10V		19		nC
Gate-Drain Charge	Q _{gd}	V _{GS} -10V		17		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =15A	-	-	1.2	V
Diode Forward Current (Note 2)	Is	-	-	-	24	А
Reverse Recovery Time	t _{rr}	TJ = 25°C, IF = 15A	-	90	-	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs ^(Note3)	-	300	-	nC

Notes:

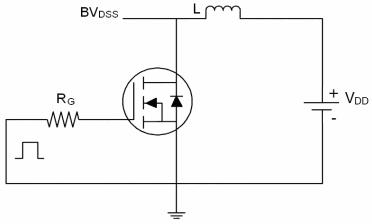
- **1.** Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition: Tj=25 $^\circ\!\mathrm{C}$,V_DD=50V,V_G=10V,L=0.5mH,Rg=25\Omega



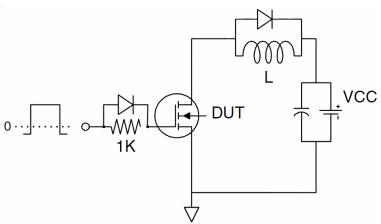
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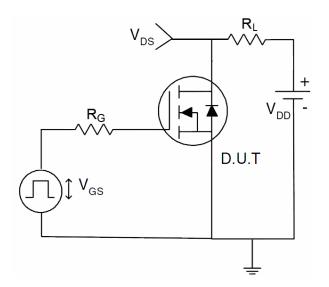
Test Circuit 1) E_{AS} Test Circuits



2) Gate Charge Test Circuit



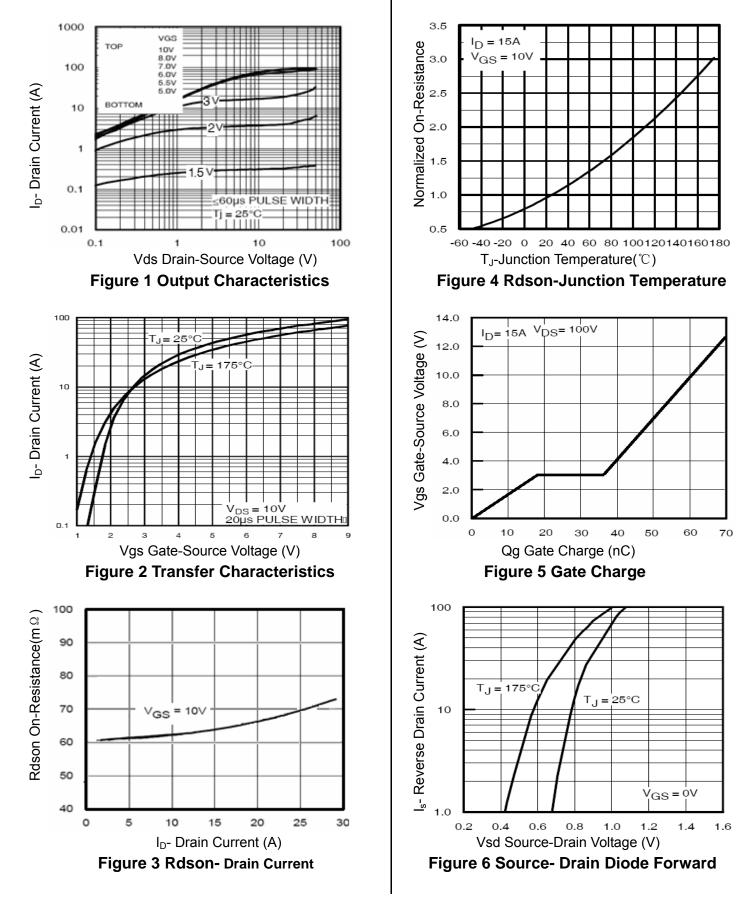
3) Switch Time Test Circuit







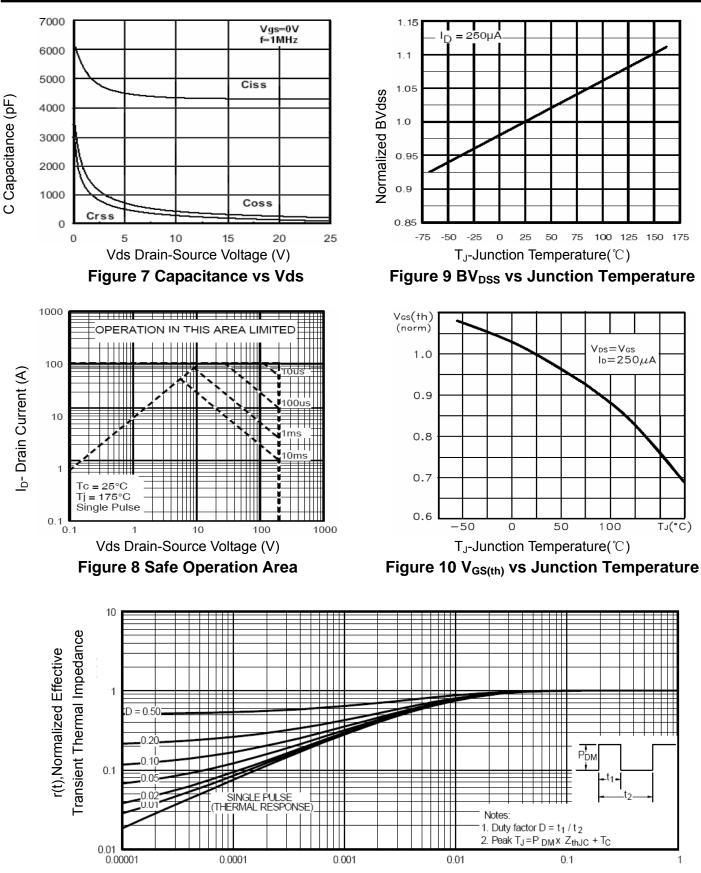
Typical Electrical and Thermal Characteristics (Curves)



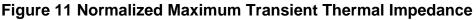


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Square Wave Pluse Duration(sec)



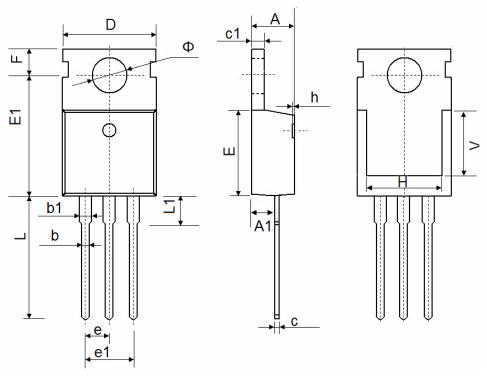
TJ(°C)



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TO-220-3L Package Information



Cumhal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Φ	3.400	3.800	0.134	0.150	





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